

Applicants : Johannes Stollenwerk et al.  
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**Amendments To The Claims:**

This listing of claims will replace all prior versions and listings of claims in the application.

1. (Previously Presented) A conductive transparent layer system with two oxide layers and a silver layer interposed therebetween on a substrate, characterized in that with a surface resistivity  $R_s$  of less than  $2.9_{sq}$ , the mean Haacke quality factor ( $\Phi_{TC} = T^{10}/R_s$ ) of the layer system for the wavelengths 435, 545 and 610 nm is greater than  $0.085^{-1}$ .
2. (Original) The layer system of claim 1, characterized in that with a surface resistivity of  $2.5_{sq}$ , the transparency  $T$  at 435 nm is at least 89%, at 545 nm at least 88% and at 610 nm at least 75%.
3. (Currently Amended) The layer system according to claim [[3]] 1, characterized in that the layer system is less than 100 nm thick, with the silver layer being less than 20 nm thick, and the two oxide layers being less than 50 nm thick.
4. (Previously Presented) The layer system according to claim 3, characterized in that the oxide layers contain about 90-95% indium and about 5-10% cerium.
5. (Previously Presented) The layer system according to claim 4, characterized in that the silver layer contains up to 10 wt. % copper.
6. (Previously Presented) The layer system according to claim 1, characterized in that the layer system is less than 100 nm thick, with the silver layer being less than 20 nm thick, and the two oxide layers being less than 50 nm thick.
7. (Previously Presented) The layer system according to claim 6, characterized in that the oxide layers contain about 90-95% indium and about 5-10% cerium.

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8. (Previously Presented) The layer system according to claim 7, characterized in that the silver layer contains up to 10 wt. % copper.

9. (Previously Presented) The layer system according to claim 1, characterized in that the oxide layers contain about 90-95 % indium and about 5-10 % cerium.

10. (Previously Presented) The layer system according to claim 9, characterized in that the silver layer contains up to 10 wt. % copper.

11. (Currently Amended) The layer system according to claim 1, characterized in that the silver layer contains up to 10 wt. copper %.

12.-20. (Canceled).

21. (Previously Presented) layer system according to claim 1 in which the second oxide layer is deposited by means of pulsed DC sputtering or AC-superimposed DC sputtering.

22. (Currently Amended) The layer system of claim [[1]] 21, characterized in that the frequency of the superimposed AC is between 1 and 50 MHz.

23. (Currently Amended) The layer system of claim [[1]] 21, characterized in that the AC component, defined by the ratio of the DC and AC power supplies, is between 10-90%.

24. (Currently Amended) The layer system of claim [[1]] 21, characterized in that the total power density (AC and DC) is in the range from 1-3 W/cm<sup>2</sup>.

25. (Currently Amended) The layer system of claim [[1]] 21, characterized in that magnetron sputtering is chosen as sputtering method.

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COMMENTS

It is believed that the above amendments merely correct errors of an obvious nature.

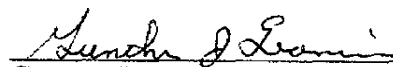
Respectfully submitted,

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December 8, 2003

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